

ON Semiconductor

Is Now

onsemi™

To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

MC33102

Two-State, Micropower Operational Amplifier

The MC33102 dual operational amplifier is an innovative design concept that has two separate states, a sleep mode and an awake mode. In sleep mode, the amplifier is active and waiting for an input signal. When a signal is applied causing the amplifier to source or sink 160 μA (typically) to the load, it will automatically switch to the awake mode which offers higher slew rate, gain bandwidth, and drive capability.

- Two States: “sleep mode” (Micropower) and “awake mode” (High Performance)
- Switches from Sleep Mode to Awake Mode in 4.0 μs when Output Current Exceeds the Threshold Current ($R_L = 600 \Omega$)
- Independent Sleep Mode Function for Each Op Amp
- Standard Pinouts – No Additional Pins or Components Required
- Sleep Mode State – Can Be Used in the Low Current Idle State as a Fully Functional Micropower Amplifier
- Automatic Return to Sleep Mode when Output Current Drops Below Threshold
- No Deadband/Crossover Distortion; as Low as 1.0 Hz in the Awake Mode
- Drop-in Replacement for Many Other Dual Op Amps
- ESD Clamps on Inputs Increase Reliability without Affecting Device Operation

TYPICAL SLEEP MODE/AWAKE MODE PERFORMANCE

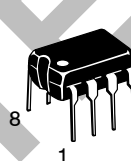
Characteristic	Sleep Mode (Typical)	Awake Mode (Typical)	Unit
Low Current Drain	45	750	μA
Low Input Offset Voltage	0.15	0.15	mV
High Output Current Capability	0.15	50	mA
Low T.C. of Input Offset Voltage	1.0	1.0	$\mu\text{V}/^\circ\text{C}$
High Gain Bandwidth (@ 20 kHz)	0.33	4.6	MHz
High Slew Rate	0.16	1.7	$\text{V}/\mu\text{s}$
Low Noise (@ 1.0 kHz)	28	9.0	$\text{nV}/\sqrt{\text{Hz}}$



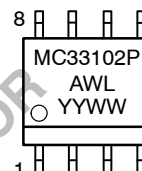
ON Semiconductor

<http://onsemi.com>

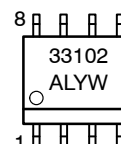
MARKING DIAGRAMS



PDIP-8
P SUFFIX
CASE 626

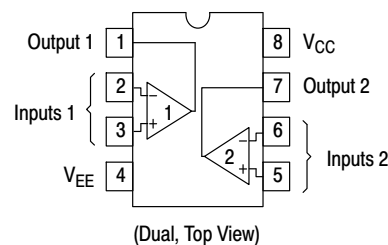


SO-8
D SUFFIX
CASE 751



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week

PIN CONNECTIONS

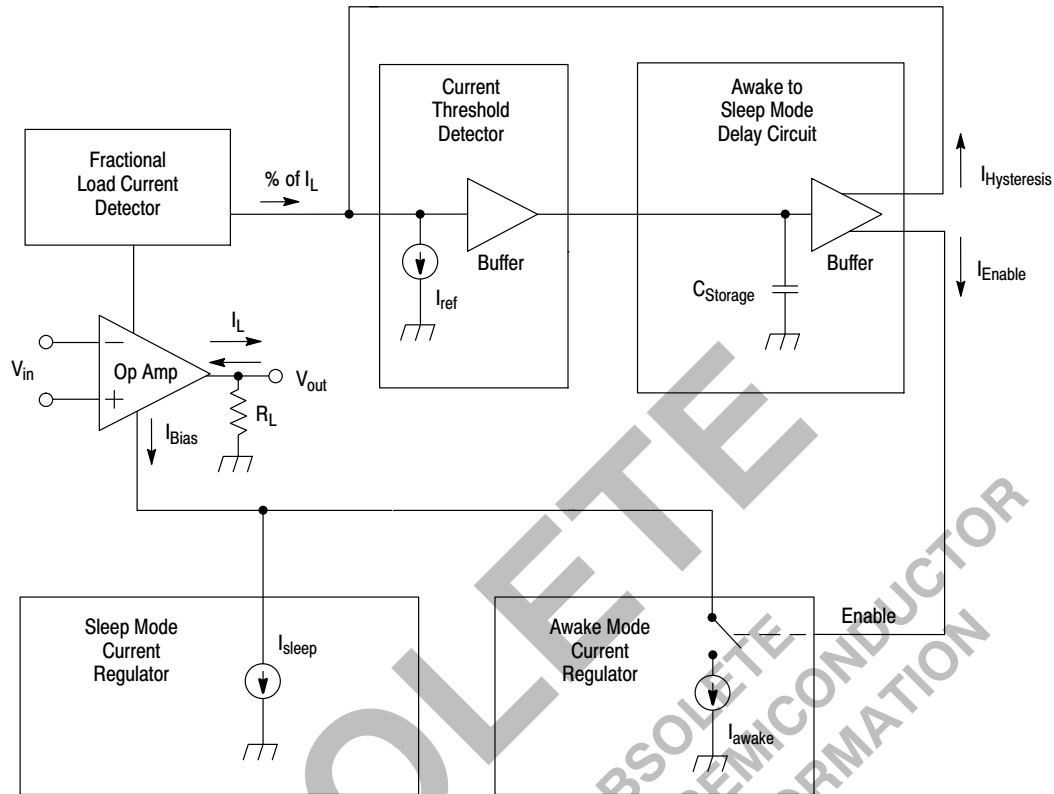


ORDERING INFORMATION

Device	Package	Shipping
MC33102D	SO-8	98 Units/Rail
MC33102DR2	SO-8	2500 Tape & Reel
MC33102P	PDIP-8	50 Units/Rail

MC33102

Simplified Block Diagram



MAXIMUM RATINGS

Ratings	Symbol	Value	Unit
Supply Voltage (V_{CC} to V_{EE})	V_S	+36	V
Input Differential Voltage Range Input Voltage Range	V_{IDR} V_{IR}	Note 1	V
Output Short Circuit Duration (Note 2)	t_{SC}	Note 2	sec
Maximum Junction Temperature Storage Temperature	T_J T_{stg}	+150 -65 to +150	°C
Maximum Power Dissipation	P_D	Note 2	mW

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Either or both input voltages should not exceed V_{CC} or V_{EE} .
2. Power dissipation must be considered to ensure maximum junction temperature (T_J) is not exceeded (refer to Figure 1).

MC33102

DC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit
Input Offset Voltage (R _S = 50 Ω, V _{CM} = 0 V, V _O = 0 V) Sleep Mode T _A = +25°C T _A = -40° to +85°C Awake Mode T _A = +25°C T _A = -40° to +85°C	2	V _{IO}	- -	0.15 -	2.0 3.0	mV
Input Offset Voltage Temperature Coefficient (R _S = 50 Ω, V _{CM} = 0 V, V _O = 0 V) T _A = -40° to +85°C (Sleep Mode and Awake Mode)	3	ΔV _{IO} /ΔT	-	1.0	-	μV/°C
Input Bias Current (V _{CM} = 0 V, V _O = 0 V) Sleep Mode T _A = +25°C T _A = -40° to +85°C Awake Mode T _A = +25°C T _A = -40° to +85°C	4, 6	I _{IB}	- -	8.0 -	50 60	nA
Input Offset Current (V _{CM} = 0 V, V _O = 0 V) Sleep Mode T _A = +25°C T _A = -40° to +85°C Awake Mode T _A = +25°C T _A = -40° to +85°C	-	I _{IO}	- -	0.5 -	5.0 6.0	nA
Common Mode Input Voltage Range (ΔV _{IO} = 5.0 mV, V _O = 0 V) Sleep Mode and Awake Mode	5	V _{ICR}	-13 -	-14.8 +14.2	- +13	V
Large Signal Voltage Gain Sleep Mode (R _L = 1.0 MΩ) T _A = +25°C T _A = -40° to +85°C Awake Mode (V _O = ±10 V, R _L = 600 Ω) T _A = +25°C T _A = -40° to +85°C	7	A _{VOL}	25 15	200 -	- -	kV/V
Output Voltage Swing (V _{ID} = ±1.0 V) Sleep Mode (V _{CC} = +15 V, V _{EE} = -15 V) R _L = 1.0 MΩ R _L = 1.0 MΩ Awake Mode (V _{CC} = +15 V, V _{EE} = -15 V) R _L = 600 Ω R _L = 600 Ω R _L = 2.0 kΩ R _L = 2.0 kΩ Awake Mode (V _{CC} = +2.5 V, V _{EE} = -2.5 V) R _L = 600 Ω R _L = 600 Ω	8, 9, 10	V _{O+} V _{O-} V _{O+} V _{O-} V _{O+} V _{O-} V _{O+} V _{O-}	+13.5 - +12.5 - +13.3 - +1.1 -	+14.2 -14.2 +13.6 -13.6 +14 -14 +1.6 -1.6	- -13.5 - -12.5 - -13.3 - -1.1	V V
Common Mode Rejection (V _{CM} = ±13 V) Sleep Mode and Awake Mode	11	CMR	80	90	-	dB
Power Supply Rejection (V _{CC} /V _{EE} = +15 V/-15 V, 5.0 V/-15 V, +15 V/-5.0 V) Sleep Mode and Awake Mode	12	PSR	80	100	-	dB

MC33102

DC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit
Output Transition Current Sleep Mode to Awake Mode (Source/Sink) (V _S = ±15 V) (V _S = ±2.5 V)	13, 14	I _{TH1}	200	160	-	μA
Awake Mode to Sleep Mode (Source/Sink) (V _S = ±15 V) (V _S = ±2.5 V)			250	200	-	
Output Short Circuit Current (Awake Mode) (V _{ID} = ±1.0 V, Output to Ground) Source Sink	15, 16	I _{SC}	50	110	-	mA
			50	110	-	
Power Supply Current (per Amplifier) (A _{CL} = 1, V _O = 0V) Sleep Mode (V _S = ±15 V) T _A = +25°C T _A = -40° to +85°C Sleep Mode (V _S = ±2.5 V) T _A = +25°C T _A = -40° to +85°C Awake Mode (V _S = ±15 V) T _A = +25°C T _A = -40° to +85°C	17	I _D	-	45	65	μA
			-	48	70	
			-	38	65	
			-	42	-	
			-	750	800	
			-	800	900	
			-	-	-	
			-	-	-	

OBSOLETE

THIS DEVICE IS OBSOLETE
PLEASE CONTACT YOUR ON SEMICONDUCTOR
REPRESENTATIVE FOR INFORMATION

MC33102

AC ELECTRICAL CHARACTERISTICS (V_{CC} = +15 V, V_{EE} = -15 V, T_A = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Typ	Max	Unit
Slew Rate (V _{in} = -5.0 V to +5.0 V, C _L = 50 pF, A _V = 1.0) Sleep mode (R _L = 1.0 MΩ) Awake mode (R _L = 600 Ω)	18	SR	0.10 1.0	0.16 1.7	- -	V/μs
Gain Bandwidth Product Sleep mode (f = 10 kHz) Awake mode (f = 20 kHz)	19	GBW	0.25 3.5	0.33 4.6	- -	MHz
Sleep mode to Awake mode Transition Time (A _{CL} = 0.1, V _{in} = 0 V to +5.0 V) R _L = 600 Ω R _L = 10 kΩ	20, 21	t _{tr1}	- -	4.0 15	- -	μs
Awake mode to Sleep mode Transition Time	22	t _{tr2}	-	1.5	-	sec
Unity Gain Frequency (Open Loop) Sleep mode (R _L = 100 kΩ, C _L = 0 pF) Awake mode (R _L = 600 Ω, C _L = 0 pF)		f _U	- -	200 2500	- -	kHz
Gain Margin Sleep mode (R _L = 100 kΩ, C _L = 0 pF) Awake mode (R _L = 600 Ω, C _L = 0 pF)	23, 25	A _M	- -	13 12	- -	dB
Phase Margin Sleep mode (R _L = 100 kΩ, C _L = 0 pF) Awake mode (R _L = 600 Ω, C _L = 0 pF)	24, 26	∅ _M	- -	60 60	- -	Degree s
Channel Separation (f = 100 Hz to 20 kHz) Sleep mode and Awake mode	29	CS	-	120	-	dB
Power Bandwidth (Awake mode) (V _O = 10 V _{pp} , R _L = 100 kΩ, THD ≤ 1%)		BW _P	-	20	-	kHz
Total Harmonic Distortion (V _O = 2.0 V _{pp} , A _V = 1.0) Awake mode (R _L = 600 Ω) f = 1.0 kHz f = 10 kHz f = 20 kHz	30	THD	- - -	0.005 0.016 0.031	- - -	%
DC Output Impedance (V _O = 0 V, A _V = 10, I _Q = 10 μA) Sleep mode Awake mode	31	R _O	- -	1.0 k 96	- -	Ω
Differential Input Resistance (V _{CM} = 0 V) Sleep mode Awake mode		R _{in}	- -	1.3 0.17	- -	MΩ
Differential Input Capacitance (V _{CM} = 0 V) Sleep mode Awake mode		C _{in}	- -	0.4 4.0	- -	pF
Equivalent Input Noise Voltage (f = 1.0 kHz, R _S = 100 Ω) Sleep mode Awake mode	32	e _n	- -	28 9.0	- -	nV/√Hz
Equivalent Input Noise Current (f = 1.0 kHz) Sleep mode Awake mode	33	i _n	- -	0.01 0.05	- -	pA/√Hz

MC33102

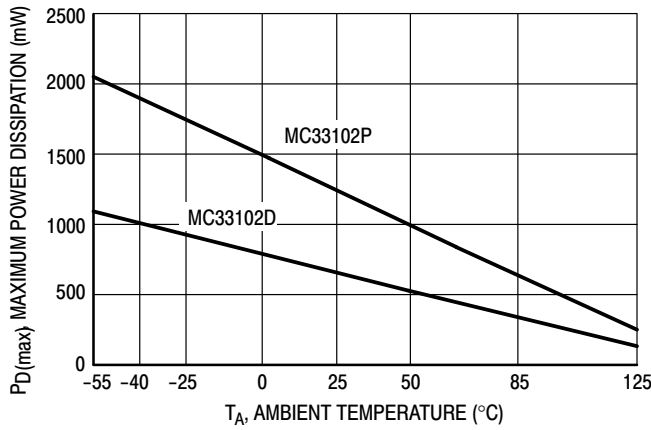


Figure 1. Maximum Power Dissipation versus Temperature

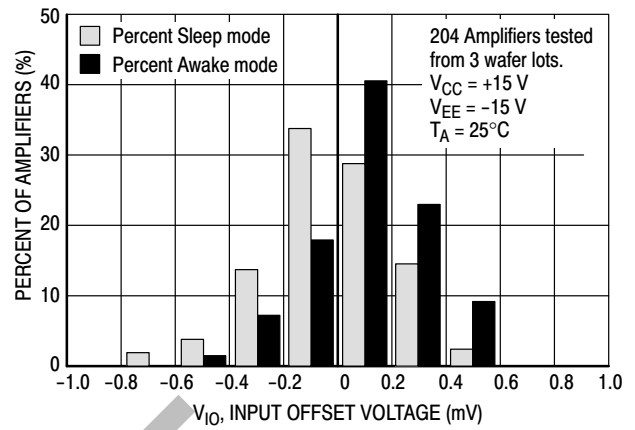


Figure 2. Distribution of Input Offset Voltage (MC33102D Package)

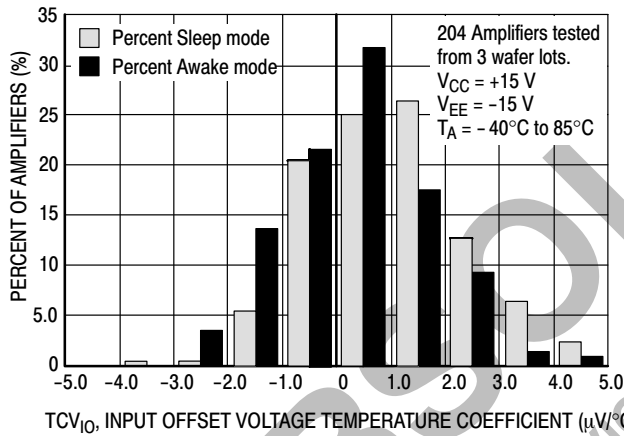


Figure 3. Input Offset Voltage Temperature Coefficient Distribution (MC33102D Package)

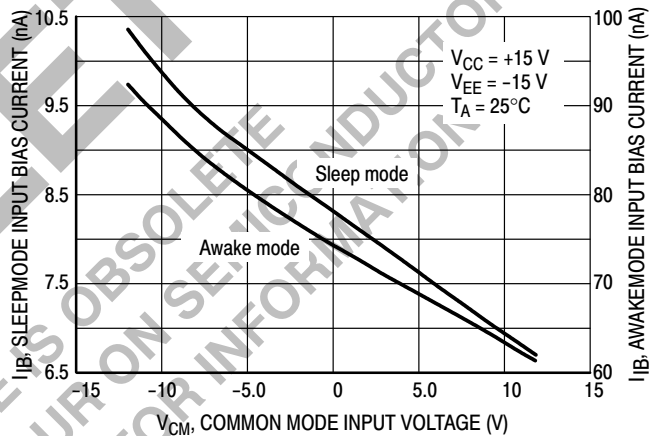


Figure 4. Input Bias Current versus Common Mode Input Voltage

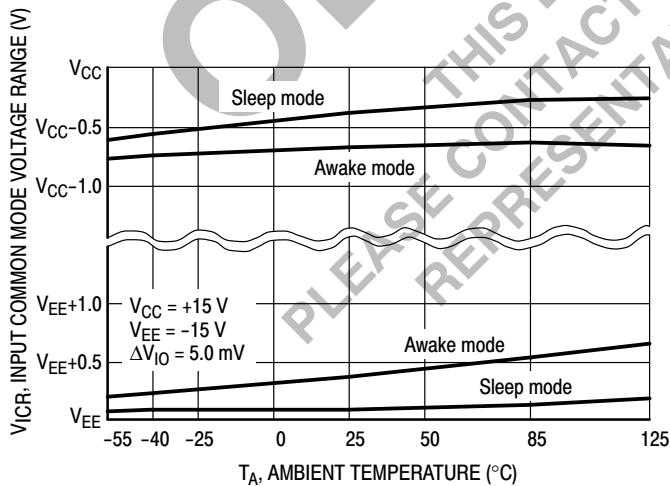


Figure 5. Input Common Mode Voltage Range versus Temperature

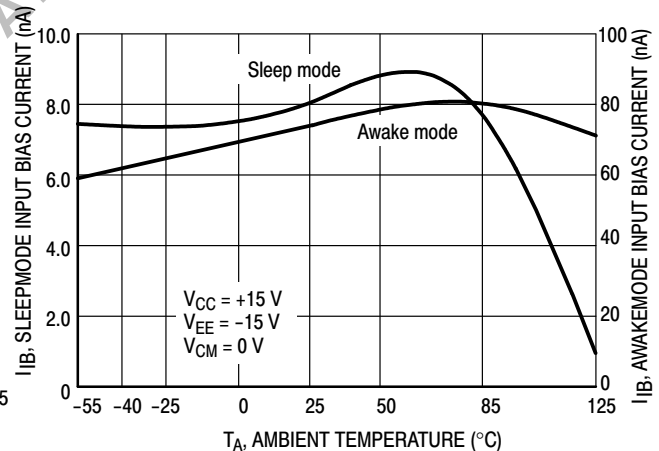


Figure 6. Input Bias Current versus Temperature

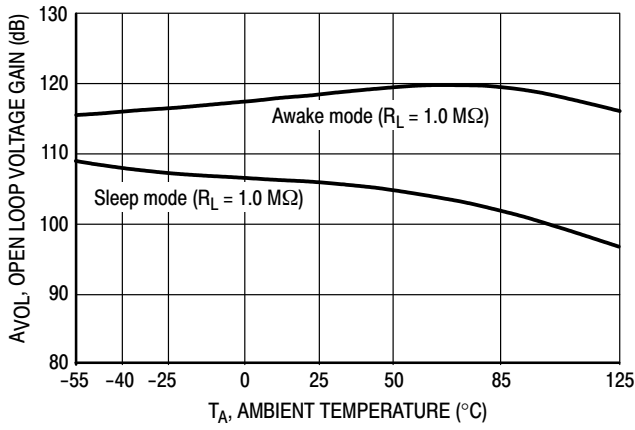


Figure 7. Open Loop Voltage Gain versus Temperature

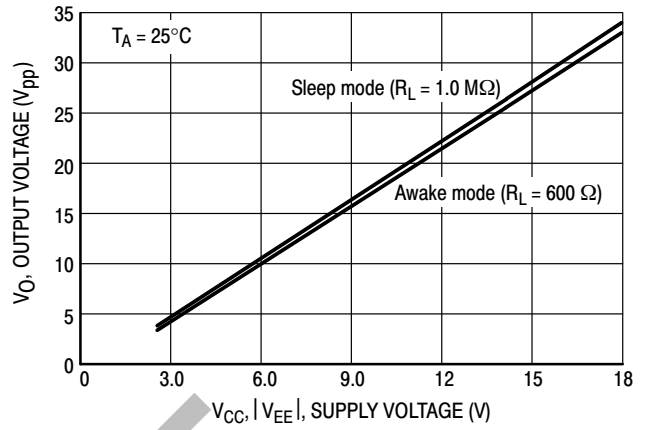


Figure 8. Output Voltage Swing versus Supply Voltage

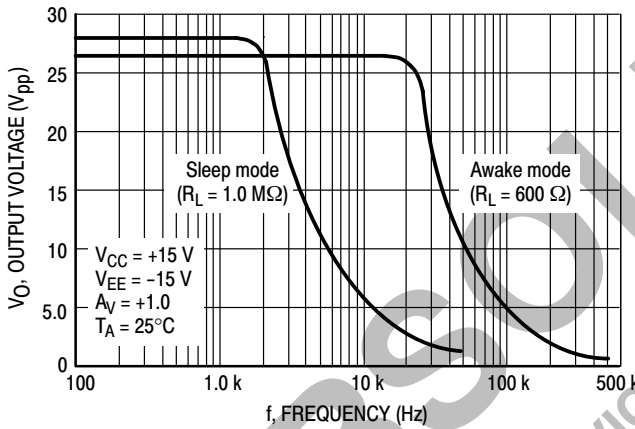


Figure 9. Output Voltage versus Frequency

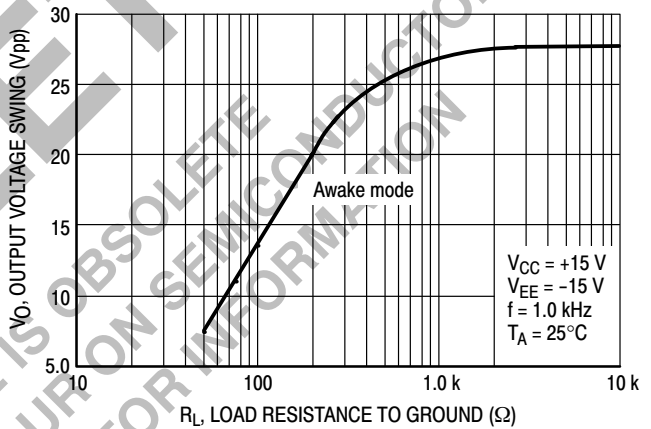


Figure 10. Maximum Peak-to-Peak Output Voltage Swing versus Load Resistance

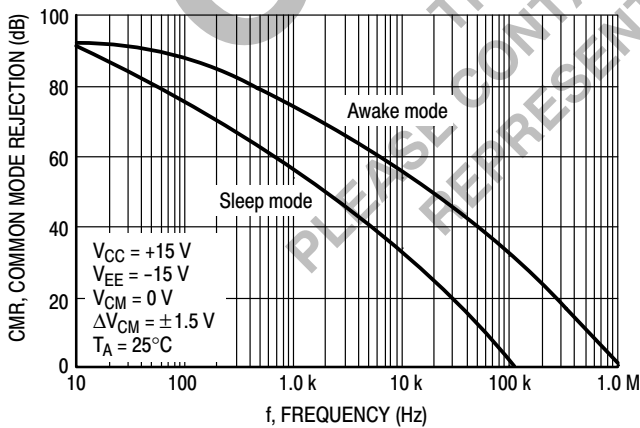


Figure 11. Common Mode Rejection versus Frequency

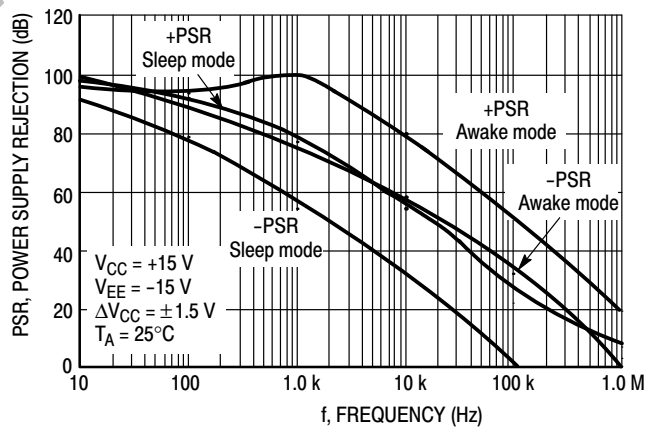


Figure 12. Power Supply Rejection versus Frequency

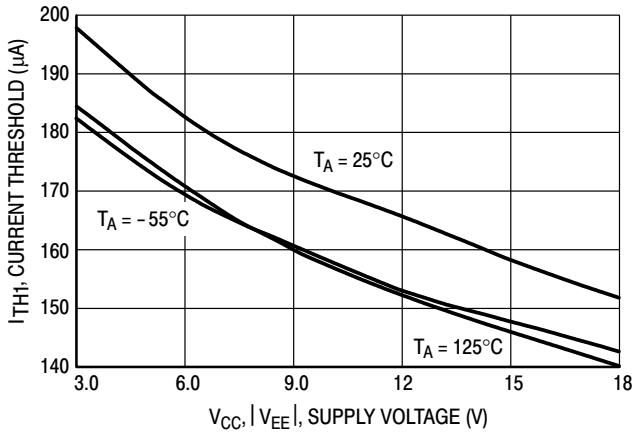


Figure 13. Sleep Mode to Awake Mode Current Threshold versus Supply Voltage

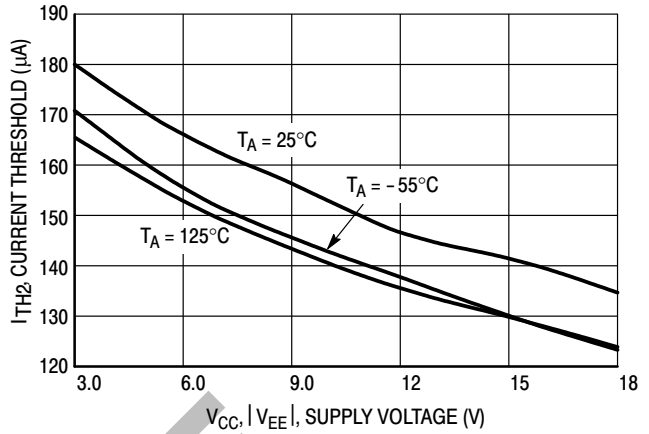


Figure 14. Awake Mode to Sleep Mode Current Threshold versus Supply Voltage

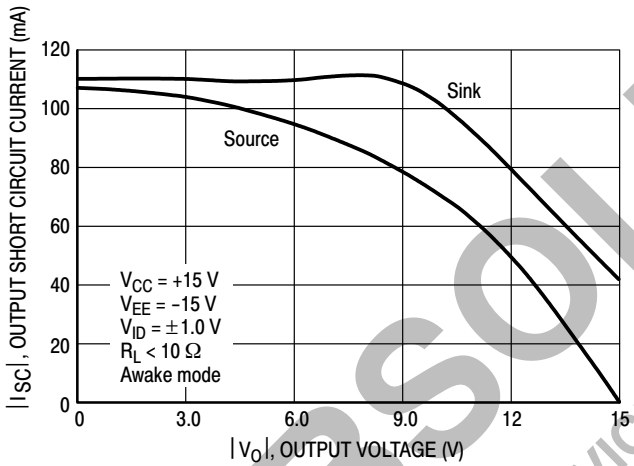


Figure 15. Output Short Circuit Current versus Output Voltage

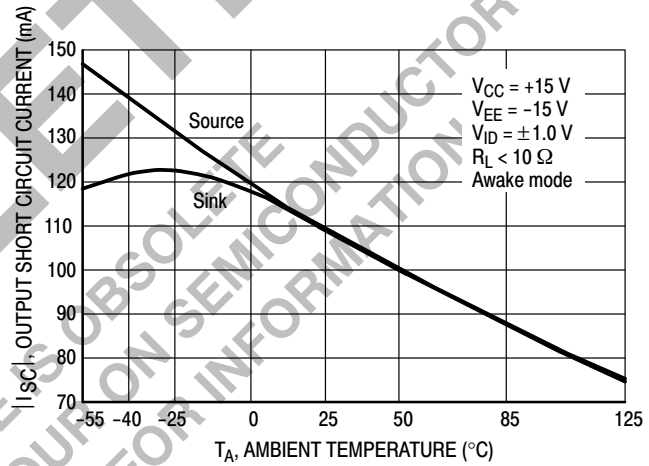


Figure 16. Output Short Circuit Current versus Temperature

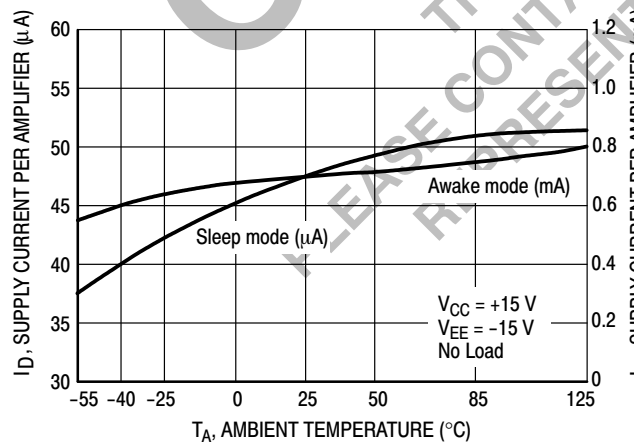


Figure 17. Power Supply Current Per Amplifier versus Temperature

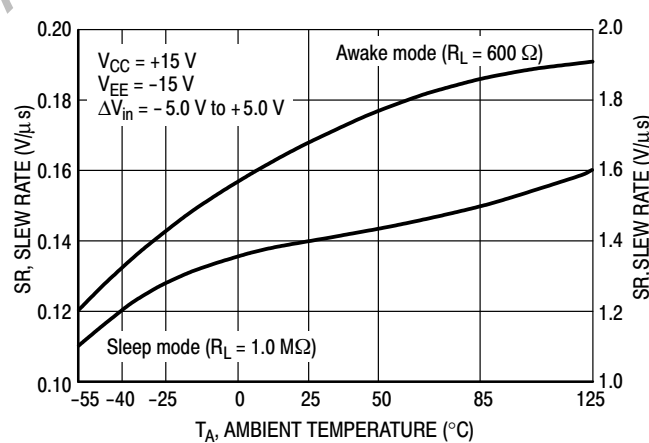


Figure 18. Slew Rate versus Temperature

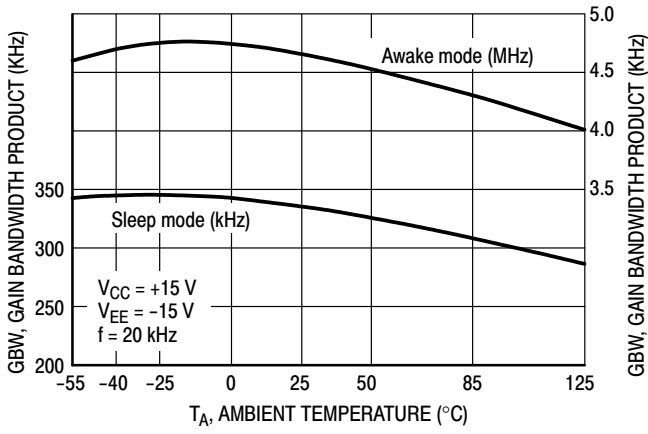


Figure 19. Gain Bandwidth Product versus Temperature

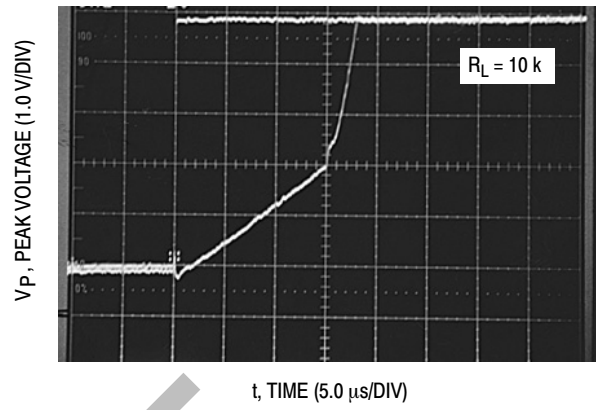


Figure 20. Sleep Mode to Awake Mode Transition Time

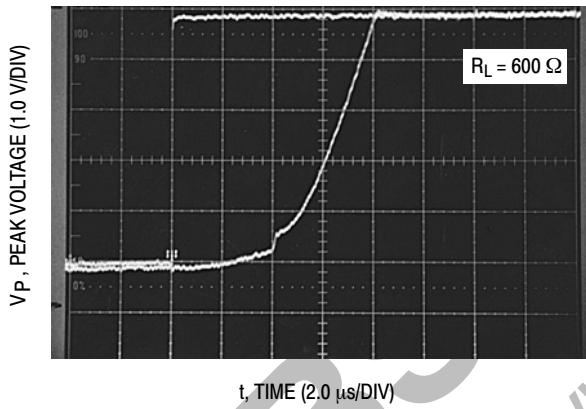


Figure 21. Sleep Mode to Awake Mode Transition Time

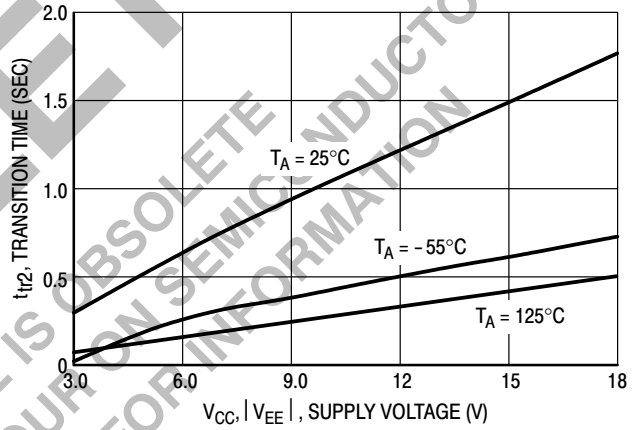


Figure 22. Awake Mode to Sleep Mode Transition Time versus Supply Voltage

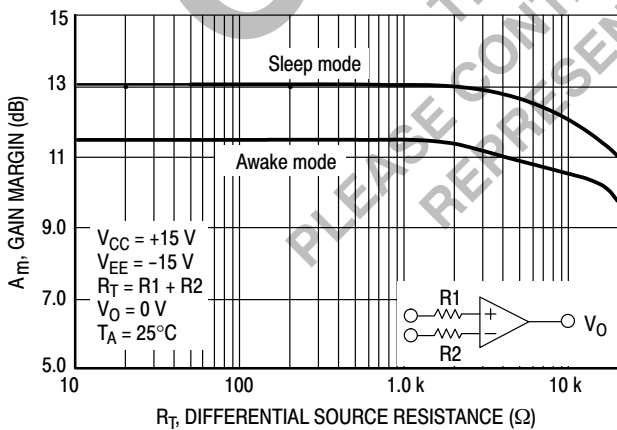


Figure 23. Gain Margin versus Differential Source Resistance

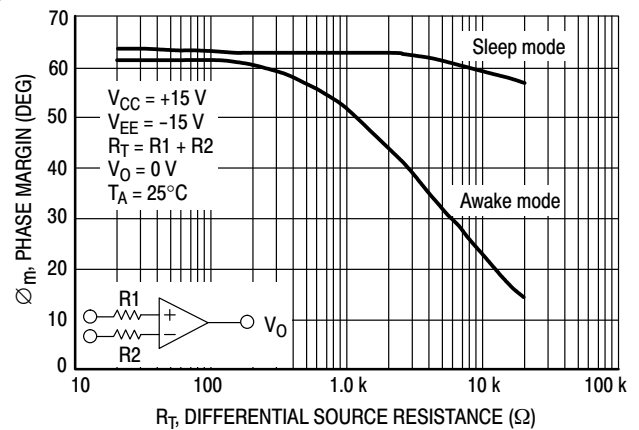


Figure 24. Phase Margin versus Differential Source Resistance

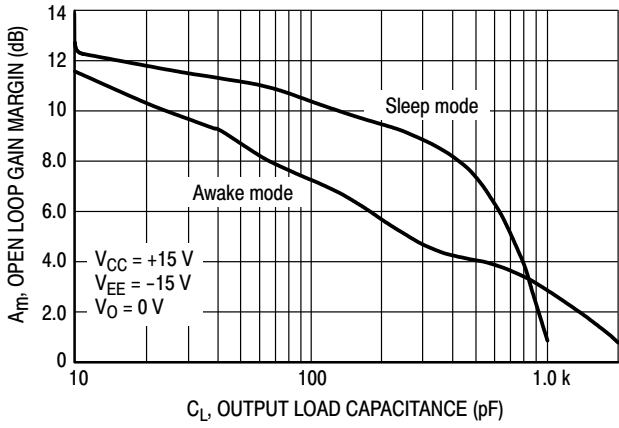


Figure 25. Open Loop Gain Margin versus Output Load Capacitance

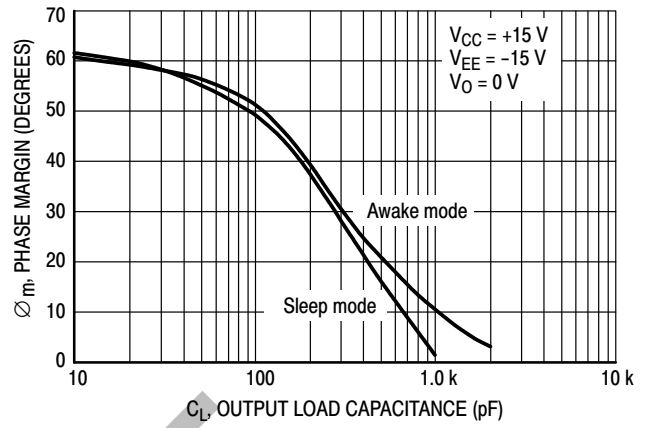


Figure 26. Phase Margin versus Output Load Capacitance

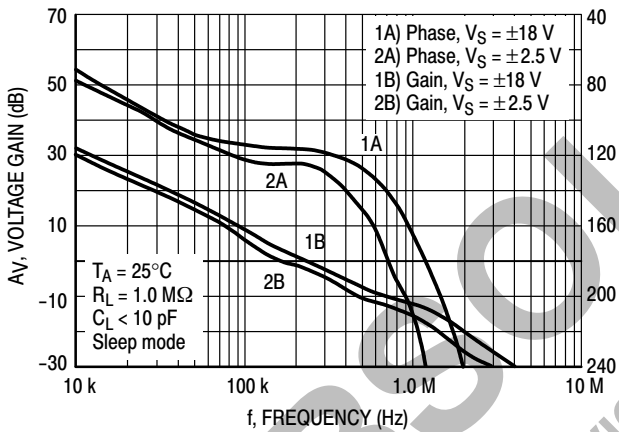


Figure 27. Sleep Mode Voltage Gain and Phase versus Frequency

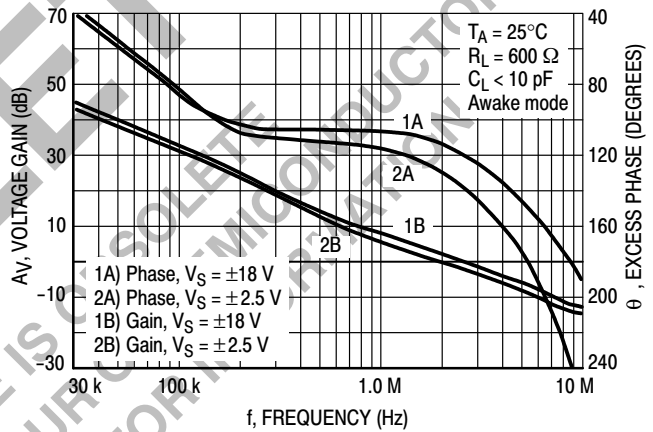


Figure 28. Awake Mode Voltage Gain and Phase versus Frequency

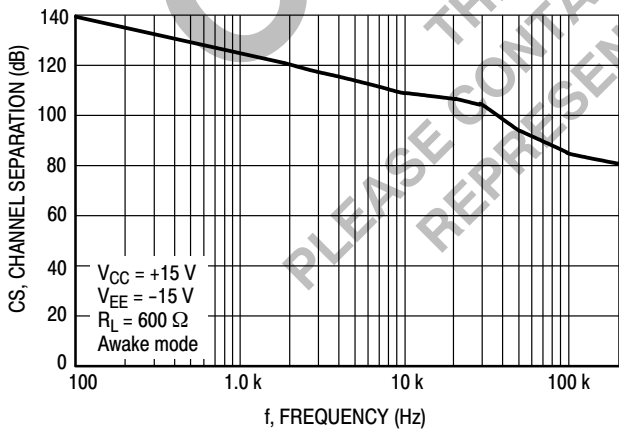


Figure 29. Channel Separation versus Frequency

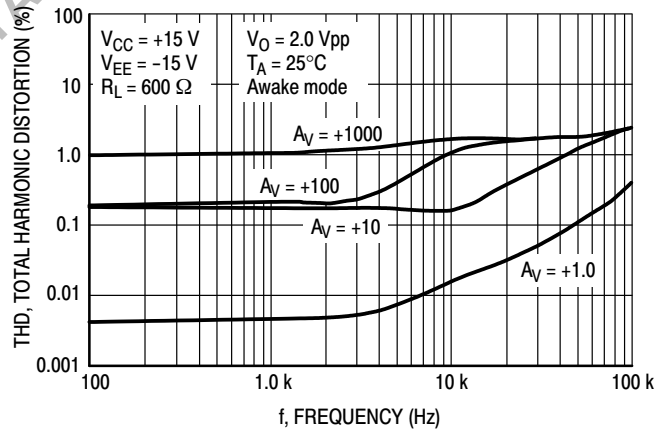


Figure 30. Total Harmonic Distortion versus Frequency

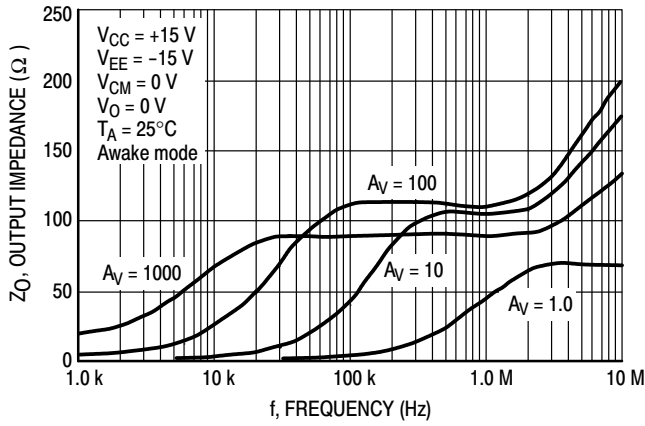


Figure 31. Awake Mode Output Impedance versus Frequency

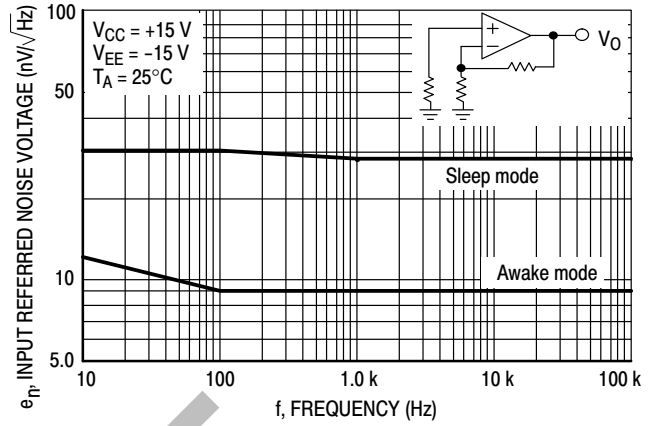


Figure 32. Input Referred Noise Voltage versus Frequency

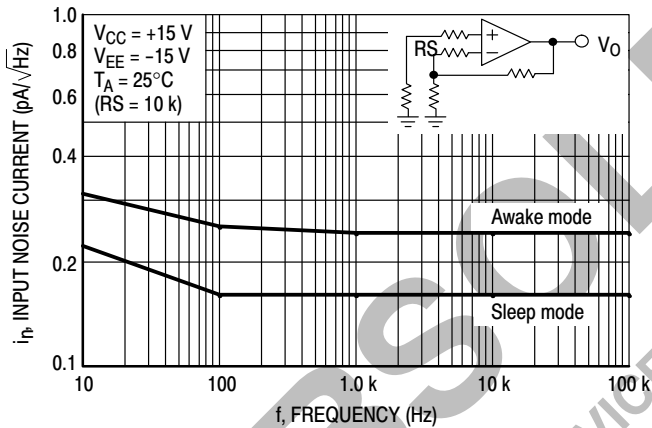


Figure 33. Current Noise versus Frequency

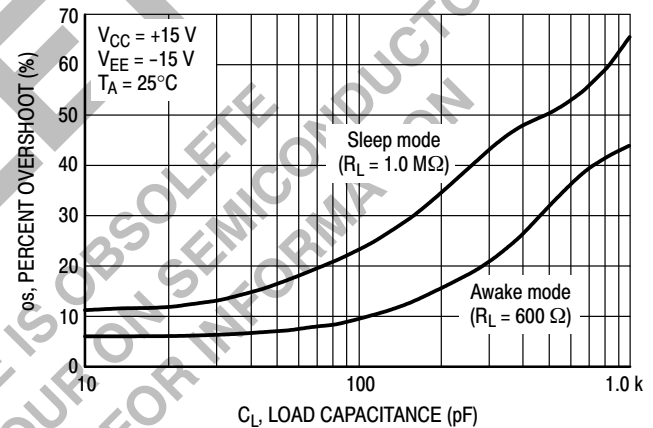


Figure 34. Percent Overshoot versus Load Capacitance

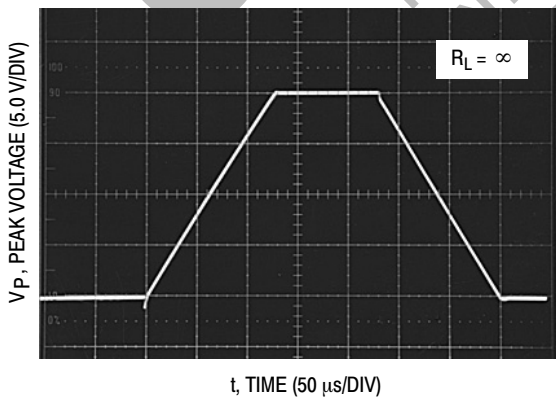


Figure 35. Sleep Mode Large Signal Transient Response

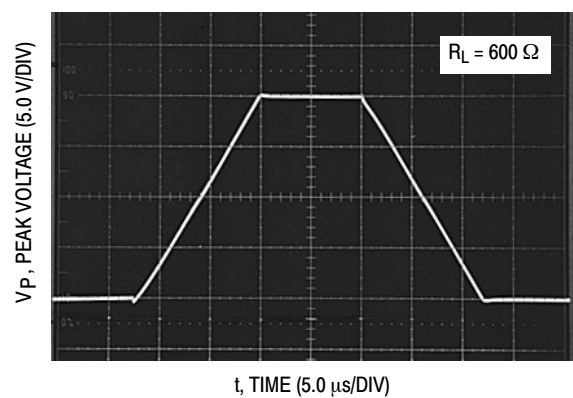


Figure 36. Awake Mode Large Signal Transient Response

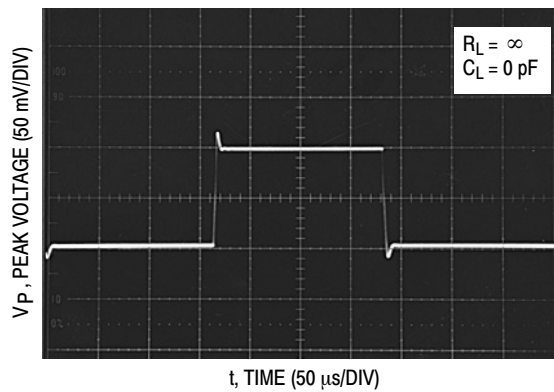


Figure 37. Sleep Mode Small Signal Transient Response

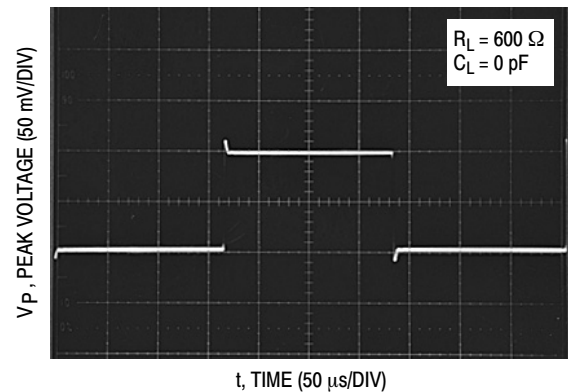


Figure 38. Awake Mode Small Signal Transient Response

CIRCUIT INFORMATION

The MC33102 was designed primarily for applications where high performance (which requires higher current drain) is required only part of the time. The two-state feature of this op amp enables it to conserve power during idle times, yet be powered up and ready for an input signal. Possible applications include laptop computers, automotive, cordless phones, baby monitors, and battery operated test equipment. Although most applications will require low power consumption, this device can be used in any application where better efficiency and higher performance is needed.

The sleep mode amplifier has two states; a sleep mode and an awake mode. In the sleep mode state, the amplifier is active and functions as a typical micropower op amp. When a signal is applied to the amplifier causing it to source or sink sufficient current (see Figure 13), the amplifier will automatically switch to the awake mode. See Figures 20 and 21 for transition times with 600 Ω and 10 kΩ loads.

The awake mode uses higher drain current to provide a high slew rate, gain bandwidth, and output current capability. In the awake mode, this amplifier can drive 27 V_{pp} into a 600 Ω load with V_S = ±15 V.

An internal delay circuit is used to prevent the amplifier from returning to the sleep mode at every zero crossing. This delay circuit also eliminates the crossover distortion commonly found in micropower amplifiers. This amplifier can process frequencies as low as 1.0 Hz without the amplifier returning to sleep mode, depending on the load.

The first stage PNP differential amplifier provides low noise performance in both the sleep and awake modes, and an all NPN output stage provides symmetrical source and sink AC frequency response.

APPLICATIONS INFORMATION

The MC33102 will begin to function at power supply voltages as low as V_S = ±1.0 V at room temperature. (At this voltage, the output voltage swing will be limited to a few hundred millivolts.) The input voltages must range between V_{CC} and V_{EE} supply voltages as shown in the maximum rating table. Specifically, **allowing the input to go more negative than 0.3 V below V_{EE} may cause product damage.** Also, exceeding the input common mode voltage range on either input may cause phase reversal, even if the inputs are between V_{CC} and V_{EE}.

When power is initially applied, the part may start to operate in the awake mode. This is because of the currents generated due to charging of internal capacitors. When this occurs and the sleep mode state is desired, the user will have to wait approximately 1.5 seconds before the device will switch back to the sleep mode. To prevent this from occurring, ramp the power supplies from 1.0 V to full supply. Notice that the device is more prone to switch into the awake mode when V_{EE} is adjusted than with a similar change in V_{CC}.

The amplifier is designed to switch from sleep mode to awake mode whenever the output current exceeds a preset current threshold (I_{TH}) of approximately 160 μA. As a result, the output switching threshold voltage (V_{ST}) is controlled by the output loading resistance (R_L). This loading can be a load resistor, feedback resistors, or both. Then:

$$V_{ST} = (160 \mu\text{A}) \times R_L$$

Large valued load resistors require a large output voltage to switch, but reduce unwanted transitions to the awake mode. For instance, in cases where the amplifier is connected with a large closed loop gain (A_{CL}), the input offset voltage (V_{IO}) is multiplied by the gain at the output and could produce an output voltage exceeding V_{ST} with no input signal applied.

Small values of R_L allow rapid transition to the awake mode because most of the transition time is consumed slewing in the sleep mode until V_{ST} is reached (see Figures 20, 21). The output switching threshold voltage V_{ST} is higher for larger values of R_L, requiring the amplifier to

slow longer in the slower sleep mode state before switching to the awake mode.

The transition time (t_{tr1}) required to switch from sleep to awake mode is:

$$t_{tr1} = t_D = I_{TH}(R_L/SR_{\text{sleepmode}})$$

Where:

t_D = Amplifier delay ($< 1.0 \mu\text{s}$)

I_{TH} = Output threshold current for more transition
($160 \mu\text{A}$)

R_L = Load resistance

$Sr_{\text{sleep mode}}$ = Sleep mode slew rate ($0.16 \text{ V}/\mu\text{s}$)

Although typically $160 \mu\text{A}$, I_{TH} varies with supply voltage and temperature. In general, any current loading on the output which causes a current greater than I_{TH} to flow will switch the amplifier into the awake mode. This includes transition currents such as those generated by charging load capacitances. In fact, the maximum capacitance that can be driven while attempting to remain in the sleep mode is approximately 1000 pF .

$$\begin{aligned} C_{L(\text{max})} &= I_{TH}/Sr_{\text{sleep mode}} \\ &= 160 \mu\text{A}/(0.16 \text{ V}/\mu\text{s}) \\ &= 1000 \text{ pF} \end{aligned}$$

Any electrical noise seen at the output of the MC33102 may also cause the device to transition to the awake mode.

To minimize this problem, a resistor may be added in series with the output of the device (inserted as close to the device as possible) to isolate the op amp from both parasitic and load capacitance.

The awake mode to sleep mode transition time is controlled by an internal delay circuit, which is necessary to prevent the amplifier from going to sleep during every zero crossing. This time is a function of supply voltage and temperature as shown in Figure 22.

Gain bandwidth product (GBW) in both modes is an important system design consideration when using a sleep mode amplifier. The amplifier has been designed to obtain the maximum GBW in both modes. "Smooth" AC transitions between modes with no noticeable change in the amplitude of the output voltage waveform will occur as long as the closed loop gains (A_{CL}) in both modes are substantially equal at the frequency of operation. For smooth AC transitions:

$$(A_{CL\text{sleep mode}}) (BW) < GBW_{\text{sleep mode}}$$

Where:

$A_{CL\text{sleep mode}}$ = Closed loop gain in the sleep mode

BW = The required system bandwidth or operating frequency

TESTING INFORMATION

To determine if the MC33102 is in the awake mode or the sleep mode, the power supply currents (I_{D+} and I_{D-}) must be measured. When the magnitude of **either** power supply current exceeds $400 \mu\text{A}$, the device is in the awake mode. When the magnitudes of both supply currents are less than $400 \mu\text{A}$, the device is in the sleep mode. Since the total supply current is typically ten times higher in the awake mode than the sleep mode, the two states are easily distinguishable.

The measured value of I_{D+} equals the I_D of both devices (for a dual op amp) plus the output source current of device A and the output source current of device B. Similarly, the measured value of I_{D-} is equal to the I_D of both devices plus

the output sink current of each device. I_{out} is the sum of the currents caused by both the feedback loop and load resistance. The total I_{out} needs to be subtracted from the measured I_D to obtain the correct I_D of the dual op amp.

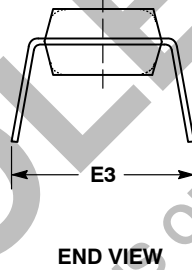
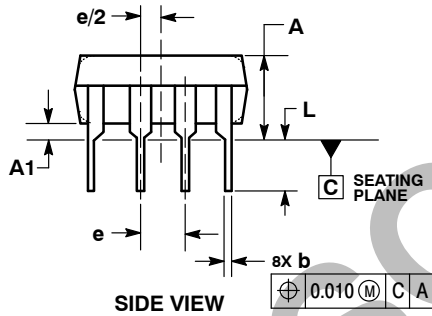
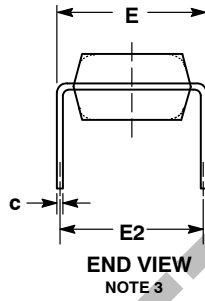
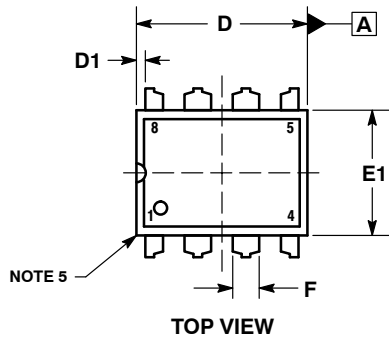
An accurate way to measure the awake mode I_{out} current on automatic test equipment is to remove the I_{out} current on both Channel A and B. Then measure the I_D values before the device goes back to the sleep mode state. The transition will take typically 1.5 seconds with $\pm 15 \text{ V}$ power supplies.

The large signal sleep mode testing in the characterization was accomplished with a $1.0 \text{ M}\Omega$ load resistor which ensured the device would remain in sleep mode despite large voltage swings.

MC33102

PACKAGE DIMENSIONS

8 LEAD PDIP
CASE 626-05
ISSUE M



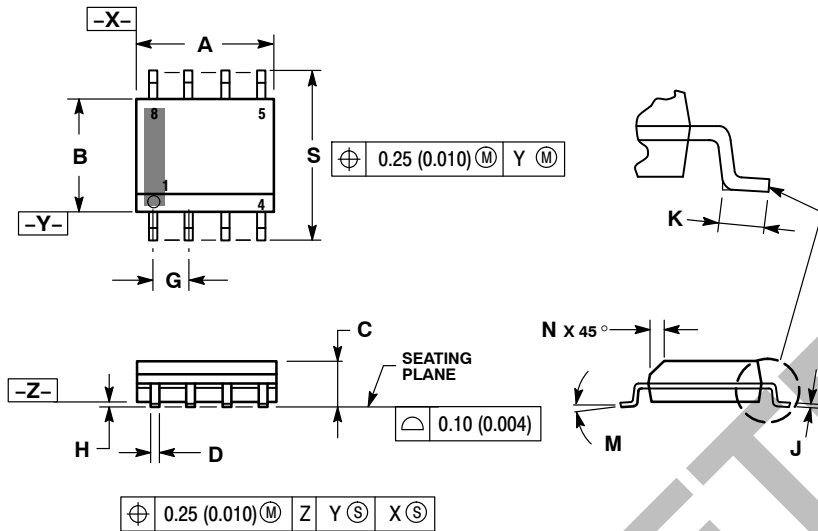
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSION E IS MEASURED WITH THE LEADS RESTRAINED PARALLEL AT WIDTH E2.
4. DIMENSION E1 DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	----	----	0.210	----	----	5.33
A1	0.015	----	----	0.38	----	----
b	0.014	0.018	0.022	0.35	0.46	0.56
C	0.008	0.010	0.014	0.20	0.25	0.36
D	0.355	0.365	0.400	9.02	9.27	10.02
D1	0.005	----	----	0.13	----	----
E	0.300	0.310	0.325	7.62	7.87	8.26
E1	0.240	0.250	0.280	6.10	6.35	7.11
E2	----	0.300 BSC	----	----	7.62 BSC	----
E3	----	----	0.430	----	----	10.92
e	----	0.100 BSC	----	----	2.54 BSC	----
L	0.115	0.130	0.150	2.92	3.30	3.81

MC33102

SOIC-8 NB
CASE 751-07
ISSUE AK

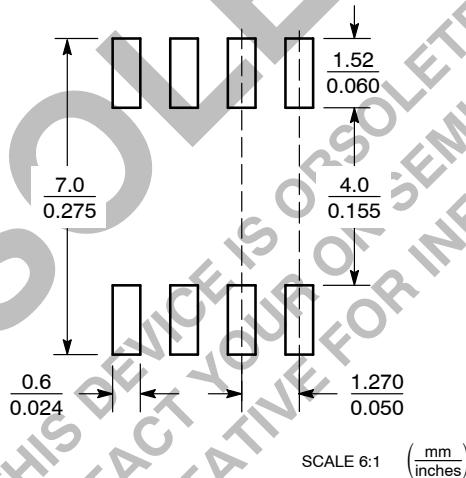


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
For additional information, please contact your local Sales Representative